

IN THE CLAIMS:

(1) Kindly cancel Claims 1, 2, 4-6, 8-15 and 25-27 without prejudice or disclaimer.

(2) Please amend Claim 16 as follows:

16. (Amended) A process for fabricating an oxide, the process comprising:

B1 (a) exposing said substrate to a first oxidizing ambient, wherein exposing said substrate to a first oxidizing ambient includes increasing from an initial temperature to a first temperature below a threshold temperature at a first ramp rate, increasing from said first temperature to a second temperature below said threshold temperature at a second ramp rate, and growing at least a portion of said oxide;

(b) exposing said substrate to a second oxidizing ambient, wherein exposing said substrate to a second oxidizing ambient includes increasing from said second temperature to a third temperature at a third ramp rate, and increasing from said third temperature to a temperature above said threshold temperature at a fourth ramp rate; and

(c) cooling said substrate to a temperature below said threshold temperature, wherein said oxide has a thickness of 15 Å or less.

REMARKS

The Applicants respectfully request reconsideration of this Application in view of the present amendment. The Applicants originally submitted Claims 1-31 in the Application. Prior to this amendment, a number of claims were amended, canceled or added. Currently, the Applicants have